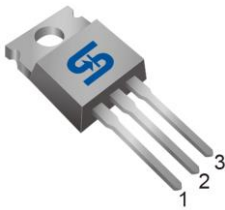


TSM80N08

75V N-Channel Power MOSFET

TO-220



Pin Definition:

1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
75	8 @ $V_{GS}=10V$	80

Features

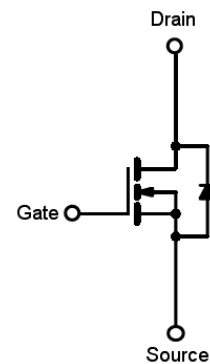
- Advanced Trench Technology
- Low $R_{DS(on)}$ 8m Ω (Max.)
- Low gate charge typical @ 91.5nC (Typ.)
- Low C_{rss} typical @ 203pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM80N08CZ C0G	TO-220	50pcs / Tube

Note: "G" denotes for Halogen Free

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	75	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	80
		$T_C=70^\circ\text{C}$	60
		$T_A=25^\circ\text{C}$	12
		$T_A=70^\circ\text{C}$	9
Drain Current-Pulsed Note 1	I_{DM}	320	A
Avalanche Current, $L=0.3\text{mH}$	I_{AS}	35	A
Avalanche Energy, $L=0.3\text{mH}$	E_{AS}	183	mJ
Maximum Power Dissipation	P_D	$T_C=25^\circ\text{C}$	113.6
		$T_C=70^\circ\text{C}$	72.7
		$T_A=25^\circ\text{C}$	2
		$T_A=70^\circ\text{C}$	1.3
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta_{JC}}$	1.1	$^\circ\text{C/W}$
Thermal Resistance - Junction to Ambient	$R_{\theta_{JA}}$	62.5	$^\circ\text{C/W}$

Notes: Surface mounted on FR4 board $t \leq 10\text{sec}$

Electrical Specifications (Ta = 25°C unless otherwise noted)

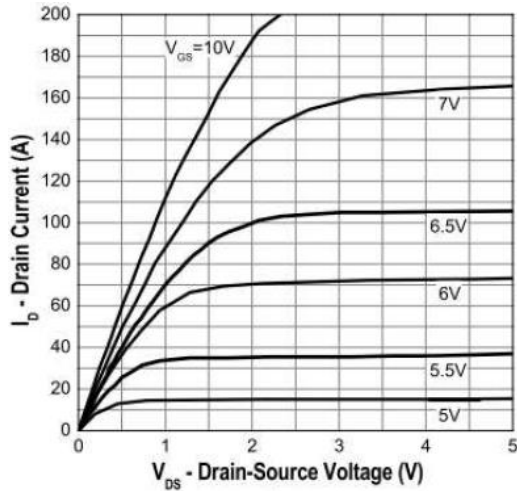
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	75	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 40A$	$R_{DS(ON)}$	--	6	8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 30V, I_D = 40A,$ $V_{GS} = 10V$	Q_g	--	91.5	--	nC
Gate-Source Charge		Q_{gs}	--	34	--	
Gate-Drain Charge		Q_{gd}	--	19.9	--	
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	3905	--	pF
Output Capacitance		C_{oss}	--	371	--	
Reverse Transfer Capacitance		C_{rss}	--	203	--	
Switching						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 30V,$ $ID = 1A, R_G = 3.3\Omega$	$t_{d(on)}$	--	21.5	--	nS
Turn-On Rise Time		t_r	--	11	--	
Turn-Off Delay Time		$t_{d(off)}$	--	73	--	
Turn-Off Fall Time		t_f	--	66	--	
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=20A$	V_{SD}	-	0.8	1.3	V
Reverse Recovery Time	$I_S = 40A, T_J=25^\circ C$ $di/dt = 100A/us$	t_{fr}		36		nS
Reverse Recovery Charge		Q_{fr}		45		nC

Notes:

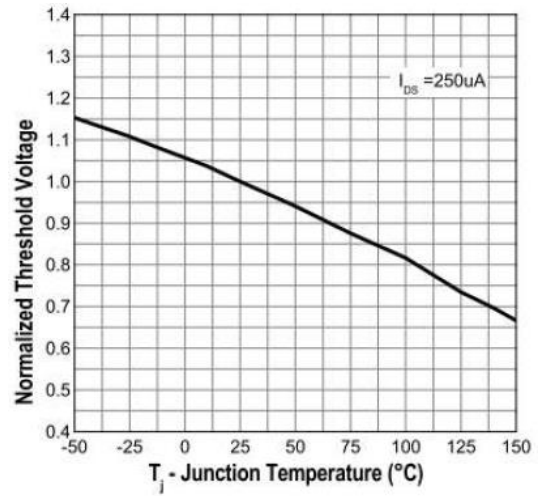
1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

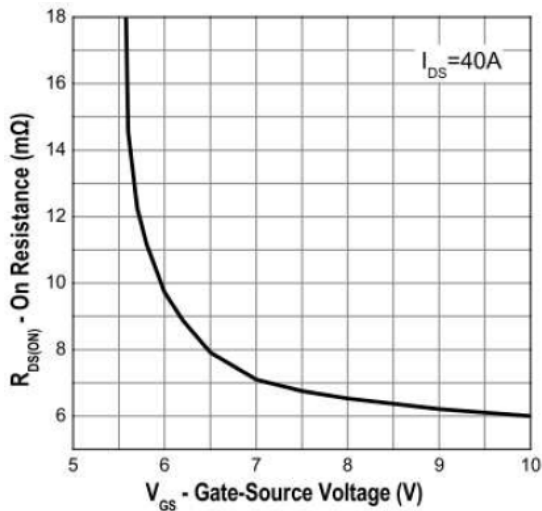
Output Characteristics



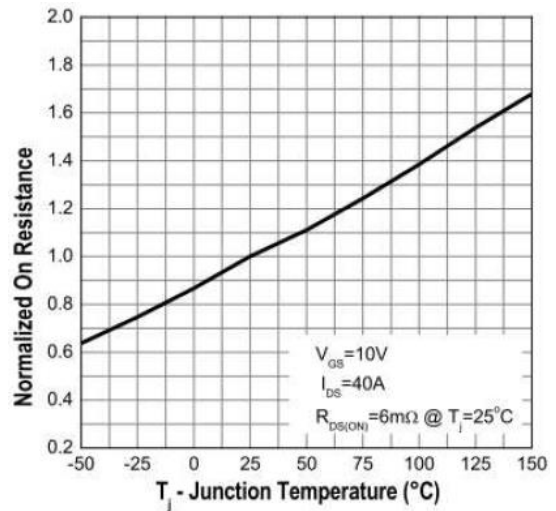
Gate Threshold Voltage



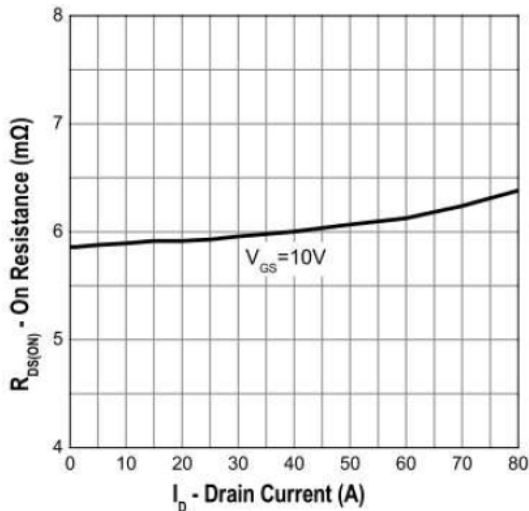
Gate Source On Resistance



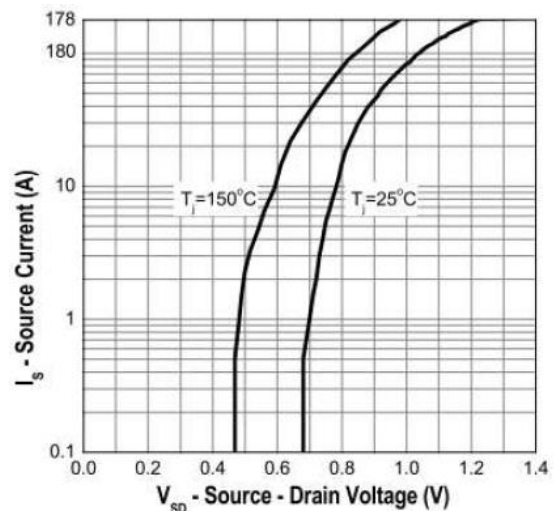
Drain-Source On Resistance



Drain-Source On-Resistance

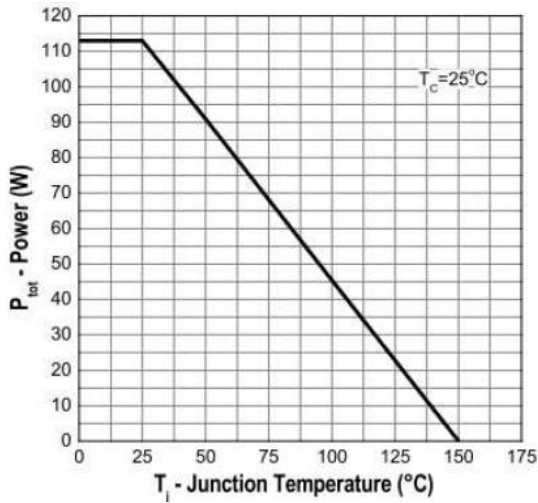


Source-Drain Diode Forward Voltage

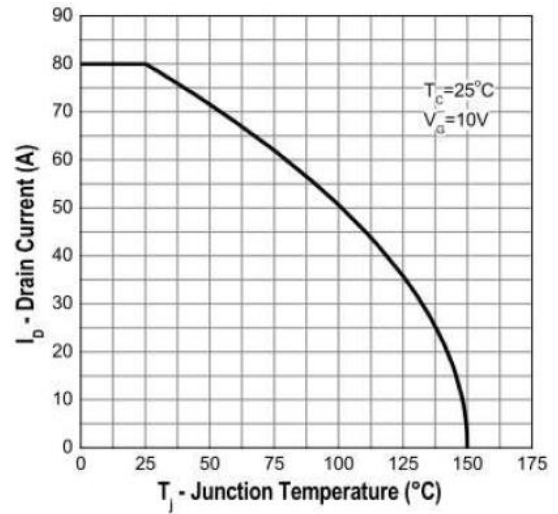


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

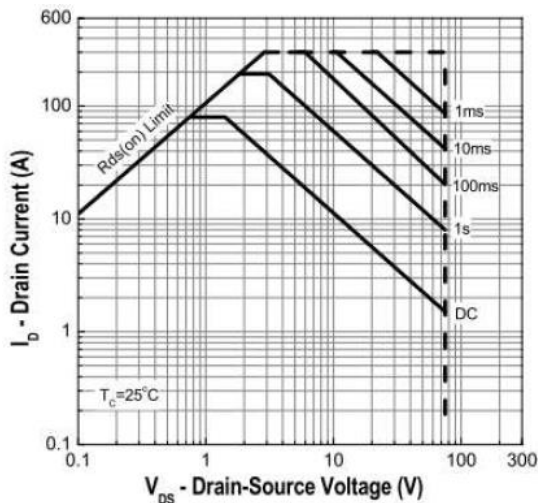
Power Derating



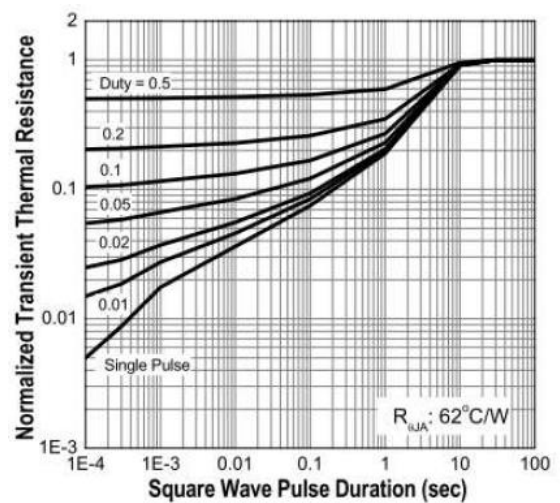
Drain Current vs. Junction Temperature



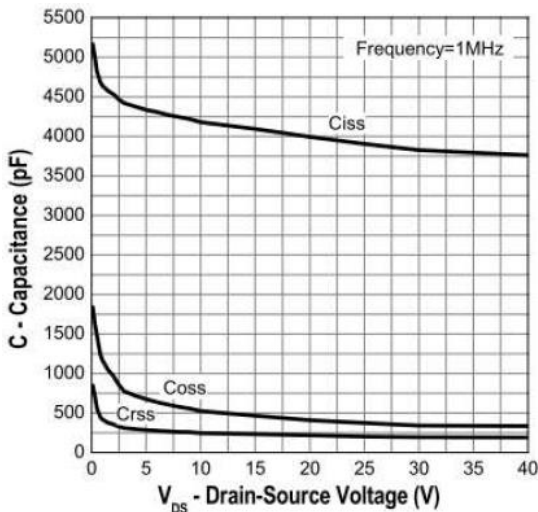
Safe Operation Area



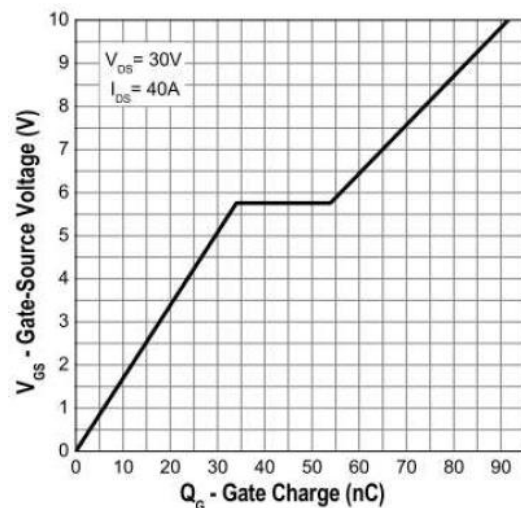
Transient Thermal Impedance



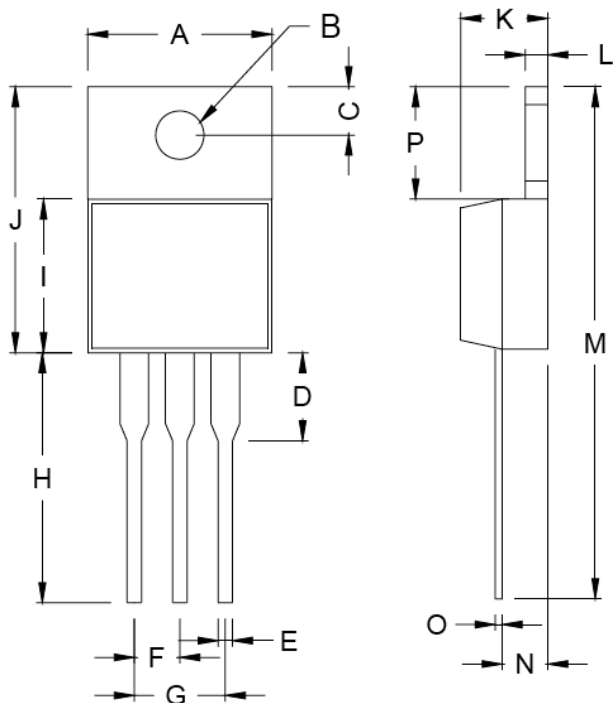
Capacitance



Gate Charge



TO-220 Mechanical Drawing



TO-220 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	10.000	10.500	0.394	0.413
B	3.740	3.910	0.147	0.154
C	2.440	2.940	0.096	0.116
D	-	6.350	-	0.250
E	0.381	1.106	0.015	0.040
F	2.345	2.715	0.092	0.058
G	4.690	5.430	0.092	0.107
H	12.700	14.732	0.500	0.581
J	14.224	16.510	0.560	0.650
K	3.556	4.826	0.140	0.190
L	0.508	1.397	0.020	0.055
M	27.700	29.620	1.060	1.230
N	2.032	2.921	0.080	0.115
O	0.255	0.610	0.010	0.024
P	5.842	6.858	0.230	0.270

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